IN THE CLAIMS

1. (cancelled)
2. (cancelled)
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16. (cancelled)
17. (cancelled)

18. (currently amended) The method of claim ~~16~~ 21 wherein the desired temperature coefficient of resistance is about zero.

19. (currently amended) The method of claim ~~16~~ 21 wherein ~~the first resistor segment is a polysilicon resistor segment that is silicided with a metal halide and the second resistor segment is an unsilicided polysilicon resistor segment, and~~ the resistor is formed as a part of a standard CMOS process flow.

20. (cancelled)

21. (new) A method for fabricating a resistor having a desired temperature coefficient of resistance and a total electrical resistance, the method comprising the steps of forming a polysilicon layer having:

a first unsilicided resistor segment having a first electrical resistance and a negative temperature coefficient of resistance, and

a second silicided resistor segment having a second electrical resistance and a positive temperature coefficient of resistance, the second segment electrically connected in series with the first segment,

where the second electrical resistance is related to the first electrical resistance according to:

$$\frac{R_1}{R_2} = \left|\frac{TCR_2}{TCR_1}\right|,$$

where R_1 is the first electrical resistance of the first resistor segment,

R_2 is the second electrical resistance of the second resistor segment,

TCR_1 is the negative temperature coefficient of resistance of the first resistor segment, and

TCR_2 is the positive temperature coefficient of resistance of the second resistor segment.

22. (new) The method of claim 21 wherein at least one of the first unsilicided resistor segment and the second silicided resistor segment is formed to be substantially rectangular.

23. (new) The method of claim 21 wherein at least one of the first unsilicided resistor segment and the second silicided resistor segment is formed to be substantially serpentine.

24. (new) The method of claim 21 wherein the total electrical resistance R_T is determined by:

$$R_T = R_2 \times \left(\left|\frac{TCR_2}{TCR_1}\right| + 1\right).$$

where R_T is the total electrical resistance of the resistor,

R_2 is the second electrical resistance of the second unsilicided resistor segment,

TCR_1 is the temperature coefficient of resistance of the first silicided resistor segment, and

TCR_2 is the temperature coefficient of resistance of the second unsilicided resistor segment.